

Appl. No. : 10/759,953
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AMENDMENTS TO THE SPECIFICATION

Please replace Paragraph 113 with the following corrected paragraph:

[0113] In another experiment, in order to remove undesirable silicon oxide, formed from TEOS as raw material, adhered inside the reaction chamber 2, 1 slm of NF_3 and 3 slm of argon were used for the cleaning gas. Fluorine active species were generated by applying 2,800 W of 400 kHz radio frequency electric power to the remote plasma discharge chamber 13. The products of this plasma, including activated fluorine species, were introduced to reaction chamber 2 from the remote plasma chamber 13. The silicon oxide was removed at a rate of about 1.5 $\mu\text{m}/\text{min}$.

Please replace Paragraph 134 with the following corrected paragraph:

[0134] In an exemplary silicon nitride deposition, about 1.5 slm ammonia (NH_3) and 15 sccm silane (SiH_4) are introduced. Nitrogen continues to flow at the same flow rate, and temperature and pressure are maintained at about 780 $^{\circ}\text{C}$ and 50 Torr. Ammonia and silane flow are continued for about 90 seconds, reacting at the substrate surface to deposit a layer of silicon nitride with a thickness of about 3 nm. As noted, one or more of the reactants can be activated through the remote plasma discharge chamber 13, thus lowering the temperature for the same deposition rate. In this case, the reaction chamber pressure is preferably reduced to facilitate plasma ignition within the remote plasma discharge chamber.